

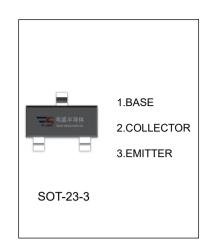
MMBT5551 TRANSISTOR (NPN)

FEATURES

- Complementary to MMBT5401
- Ideal for Medium Power Amplification and Switching

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

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Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	180	V
V _{CEO}	Collector-Emitter Voltage	160	V
V _{EBO}	Emitter-Base Voltage	6	V
Ic	Collector Current	600	mA
Pc	Collector Power Dissipation	300	mW
R _{OJA}	Thermal Resistance From Junction To Ambient	416	°C/W
T_J, T_stg	Operation Junction and Storage Temperature Range	-55~+150	℃



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	180			V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =1mA, I _B =0	160			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =120V, I _E =0			50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			50	nA
	h _{FE(1)} *	V _{CE} =5V, I _C =1mA	80			
DC current gain	h _{FE(2)} *	V _{CE} =5V, I _C =10mA	100		300	
	h _{FE(3)} *	V _{CE} =5V, I _C =50mA	50			
Collector emitter saturation voltage	V _{CE(sat)1} *	I _C =10mA, I _B =1mA			0.15	V
Collector-emitter saturation voltage	V _{CE(sat)2} *	I _C =50mA, I _B =5mA			0.2	V
Base-emitter saturation voltage	V _{BE(sat)1} *	I _C =10mA, I _B =1mA			1	V
Base-enniter saturation voitage	V _{BE(sat)2} *	I _C =50mA, I _B =5mA			1	V
Transition frequency	f _T	V _{CE} =10V,I _C =10mA, f=100MHz	100		300	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			6	pF

^{*}Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

CLASSIFICATION OF h_{FE (2)}

RANK	L	н
RANGE	100-200	200-300



